

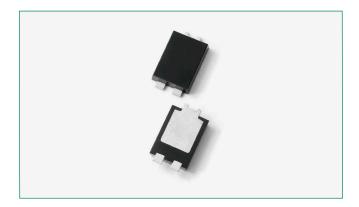
# DST580S-A



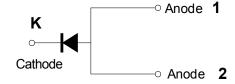








#### Pin out



#### **Description**

Littelfuse DST series Ultra Low V<sub>E</sub> Schottky Barrier Rectifier is designed to meet the general requirements of automotive applications by providing high temperature, low leakage and lower V<sub>E</sub> products.

It is suitable for high frequency switching mode power supply, free-wheeling diodes and polarity protection diodes.

#### **Features**

- High reliability application and AEC-Q101 qualified
- Ultra low forward voltage
- High frequency operation
- MSL: Level 1 unlimited
- High junction temperature capability
- Trench MOS Schottky technology

- Single die in TO-277B Package
- Pb-free E3 means 2nd level interconnect is Pb-free and the terminal finish material is tin(Sn) (IPC/ JEDEC J-STD-609A.01)

#### **Applications**

- Switching mode power
- DC/DC converters
- Free-Wheeling diodes
- Polarity Protection Diodes

#### **Maximum Ratings**

Parameters	Symbol	Test Conditions	Max	Unit
Peak Inverse Voltage	V <sub>RWM</sub>	-	80	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>L</sub> = 125 °C rectangular wave form	5	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	80	А

#### **Electrical Characteristics**

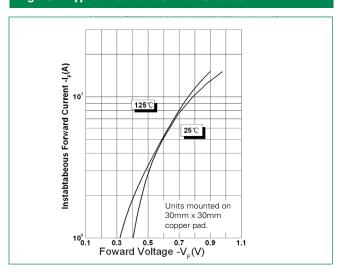
Parameters	Symbol	Test Conditions	Тур	Max	Unit	
	V	@2.5A, Pulse, T <sub>J</sub> = 25 °C	0.48	-		
Forward Voltage Drop*	V <sub>F1</sub>	@5A, Pulse, T <sub>J</sub> = 25 °C	0.59	0.72	V	
roi watu voitage Diop		@2.5A, Pulse, T <sub>J</sub> = 125 °C	0.45	-	V	
	V <sub>F2</sub>	@5A, Pulse, T <sub>J</sub> = 125 °C	0.59	0.66		
Reverse Current*	I <sub>R1</sub>	$@V_R = rated V_R, T_J = 25 °C$	0.011	0.4	mA	
neverse Current	I <sub>R2</sub>	$@V_R = rated V_{R_i} T_J = 125  ^{\circ}C$	4	15	- IIIA	
Junction Capacitance	C <sub>T</sub>	$@V_R = 5V, T_C = 25  ^{\circ}C, f_{SIG} = 1MHz$	245	-	pF	

<sup>\*</sup> Pulse Width < 300µs, Duty Cycle <2%

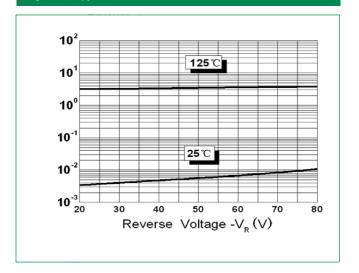


Thermal-Mechanical Specifications					
Parameters	Symbol	Test Conditions	Max	Unit	
Junction Temperature	T <sub>J</sub>		-55 to +150	°C	
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C	
Maximum Thermal Resistance Junction to Ambient	R <sub>thJA</sub>	DC eneration	75	°C/W	
Maximum Thermal Resistance Junction to Lead	R <sub>thJL</sub>	DC operation	4	°C/W	
Approximate Weight	wt		0.08	g	
Case Style	TO-277B				

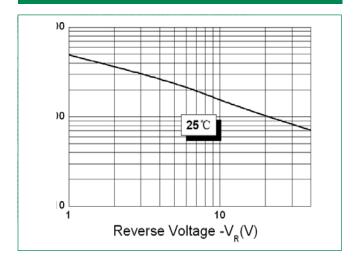
#### Figure 1: Typical Forward Characteristics



**Figure 2: Typical Reverse Characteristics** 

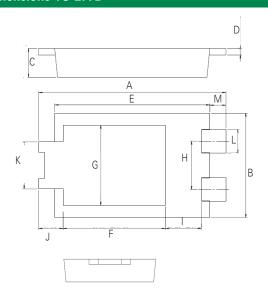


**Figure 3: Typical Junction Capacitance** 



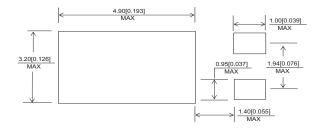


## **Dimensions-TO-277B**



Symbol	Millimeters			
Symbol	Min	Тур	Max	
А	6.30	6.50	6.70	
В	3.88	3.98	4.08	
С	0.95	1.10	1.25	
D	0.20	0.25	0.30	
E	5.28	5.38	5.48	
F	3.40	3.55	3.70	
G	2.90	3.05	3.20	
Н	1.74	1.84	1.94	
I	1.10	1.25	1.40	
J	-	0.85	-	
K	1.70	1.80	1.90	
L	0.85	0.90	0.95	
М	-	0.56	-	

#### **Mounting Pad Layout**



## **Packing Options**

Part Number	Marking	Packing Mode	M.O.Q	
DST580S-A	DST580S-A	5000pcs / Reel	5000	

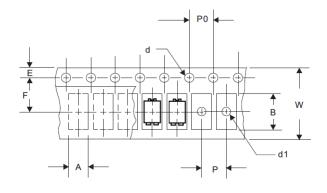
#### **Part Numbering and Marking System**



DST = Device Type
5 = Forward Current (5A)
80 = Reverse Voltage (80V)
S = Package Type
A = AEC-Q101 qualified device
LF = Littelfuse
YY = Year

WW = Week
L = Lot Number

# **Carrier Tape & Reel Specification**



Symbol	Millimeters		
Cymbol	Min	Max	
А	4.28	4.48	
В	6.80	7.00	
d	1.40	1.60	
d1	-	1.50	
Е	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
W	11.70	12.30	

# **Mouser Electronics**

**Authorized Distributor** 

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Littelfuse:
DST580S-A